# N-Channel 40 V (D-S) MOSFET

| PRODUCT SUMMARY | | | |
|---|---|---|---|
| $V_{DS}$ (V) | $R_{DS(on)}$ (mΩ)(Typ.) | $I_D$ (A)[a] | $Q_g$ (Typ.) |
| 40 | 2.2 at $V_{GS}$ = 10 V | 125 | 40.4 nC |
| | 3.3 at $V_{GS}$ = 4.5 V | | |

## FEATURES

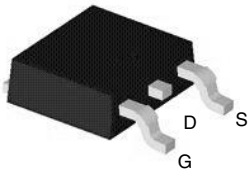
- DT-Trench Power MOSFET
- 100 % $R_g$ and UIS Tested
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current

RoHS COMPLIANT

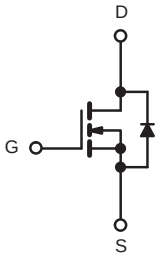
## APPLICATIONS

- Load switching
- Hard switched and high frequency circuits

TO-252 Pin Configuration




Top View




N-Channel MOSFET

| ABSOLUTE MAXIMUM RATINGS ($T_C$ = 25 °C, unless otherwise noted) | | | | |
|---|---|---|---|---|
| PARAMETER | | SYMBOL | LIMIT | UNIT |
| Drain-Source Voltage | | $V_{DS}$ | 40 | V |
| Gate-Source Voltage | | $V_{GS}$ | ± 20 | |
| Continuous Drain Current ($T_J$ = 175 °C)[a] | $T_C$ = 25 °C | $I_D$ | 125 | A |
| | $T_C$ = 100 °C | | 110 | |
| Pulsed Drain Current[b] | | $I_{DM}$ | 400 | |
| Single Avalanche Energy | | $E_{AS}$ | 255 | mJ |
| Maximum Power Dissipation[c] | $T_C$ = 25 °C | $P_D$ | 150 | W |
| | $T_C$ = 100 °C | | 75 | |
| Operating Junction and Storage Temperature Range | | $T_J$, $T_{stg}$ | - 55 to + 175 | °C |

| THERMAL RESISTANCE RATINGS | | | |
|---|---|---|---|
| PARAMETER | SYMBOL | LIMIT | UNIT |
| Junction-to-Ambient (PCB Mount)[d] | $R_{thJA}$ | 45 | °C/W |
| Junction-to-Case (Drain) | $R_{thJC}$ | 1 | |

**Notes**

a. Calculated continuous current based on maximum allowablejunction temperature.
b. Repetitive rating; pulse width limited by max. junction temperature.
c. Pd is based on max. junction temperature, using junction-case thermal resistance.
d. The value of $R_{\theta JA}$ is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper,in a still air environment with Ta=25 °C.

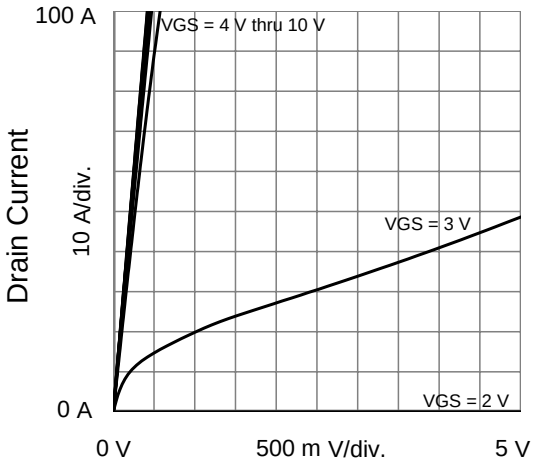
| SPECIFICATIONS ($T_C$ = 25 °C, unless otherwise noted) | | | | | | |
|---|---|---|---|---|---|---|
| **PARAMETER** | **SYMBOL** | **TEST CONDITIONS** | **MIN.** | **TYP.** | **MAX.** | **UNIT** |
| **Static** | | | | | | |
| Drain-Source Breakdown Voltage | $V_{DS}$ | $V_{GS}$ = 0 V, $I_D$ = 250 µA | 40 | - | - | V |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS}$ = $V_{GS}$, $I_D$ = 250 µA | 1 | - | 3 | |
| Gate-Body Leakage | $I_{GSS}$ | $V_{DS}$ = 0 V, $V_{GS}$ = ± 20 V | - | - | ± 100 | nA |
| Zero Gate Voltage Drain Current | $I_{DSS}$ | $V_{DS}$ = 40 V, $V_{GS}$ = 0 V | - | - | 1 | µA |
| | | $V_{DS}$ = 40 V, $V_{GS}$ = 0 V, $T_J$ = 125 °C | - | - | 100 | |
| On-State Drain Current [a] | $I_{D(on)}$ | $V_{DS}$ ≥ 5 V, $V_{GS}$ = 10 V | 125 | - | - | A |
| Drain-Source On-State Resistance [a] | $R_{DS(on)}$ | $V_{GS}$ = 10 V, $I_D$ = 30 A | - | 2.2 | 2.7 | mΩ |
| | | $V_{GS}$ = 4.5 V, $I_D$ = 30 A | - | 3.3 | 3.8 | |
| Forward Transconductance [a] | $g_{fs}$ | $V_{DS}$ = 5 V, $I_D$ = 30 A | - | 55 | - | S |
| **Dynamic [b]** | | | | | | |
| Input Capacitance | $C_{iss}$ | $V_{GS}$ = 0 V, $V_{DS}$ = 20 V, f = 1 MHz | - | 2920 | - | pF |
| Output Capacitance | $C_{oss}$ | | - | 876 | - | |
| Reverse Transfer Capacitance | $C_{rss}$ | | - | 2 | - | |
| Total Gate Charge [c] | $Q_g$ | $V_{DS}$ = 20 V, $V_{GS}$ = 10 V, $I_D$ = 30 A | - | 40.4 | - | nC |
| Gate-Source Charge [c] | $Q_{gs}$ | | - | 5.84 | - | |
| Gate-Drain Charge [c] | $Q_{gd}$ | | - | 4.96 | - | |
| Gate Resistance | $R_g$ | f = 1 MHz | - | 4.4 | - | Ω |
| Turn-On Delay Time [c] | $t_{d(on)}$ | $V_{DD}$ = 20 V, $I_D$ = 30 A, $R_g$ = 3 Ω, $V_{GS}$ = 10 V | - | 11.5 | - | ns |
| Rise Time [c] | $t_r$ | | - | 10 | - | |
| Turn-Off Delay Time [c] | $t_{d(off)}$ | | - | 40 | - | |
| Fall Time [c] | $t_f$ | | - | 12 | - | |
| **Drain-Source Body Diode Ratings and Characteristics [b]** ($T_C$ = 25 °C) | | | | | | |
| Continuous Source-Drain Diode Current | $I_S$ | $T_C$ = 25 °C | - | - | 125 | A |
| Pulsed Current | $I_{SM}$ | | - | - | 400 | A |
| Forward Voltage [a] | $V_{SD}$ | $I_F$ = 1 A, $V_{GS}$ = 0 V | - | - | 1.2 | V |
| Reverse Recovery Time | $t_{rr}$ | $I_F$ = 30 A, di/dt = 100 A/µs | - | 23 | - | ns |
| Reverse Recovery Charge | $Q_{rr}$ | | - | 55 | - | nC |

**Notes**

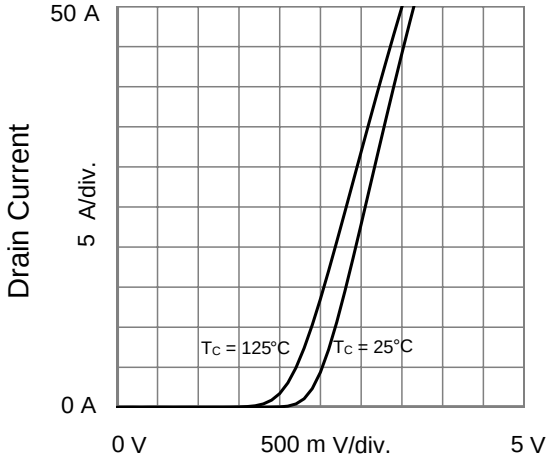
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

*Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.*

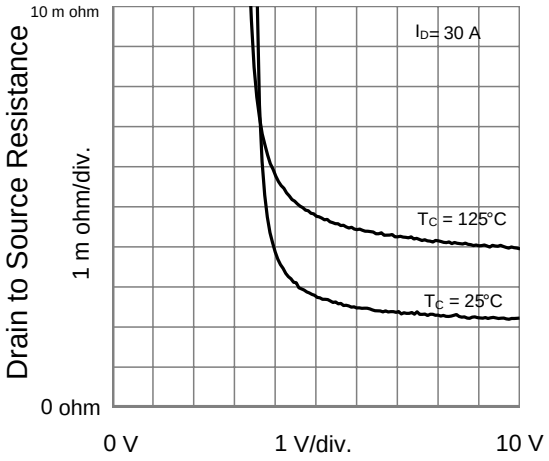
**TYPICAL CHARAC TERISTICS** (25 °C, unless otherwise noted)



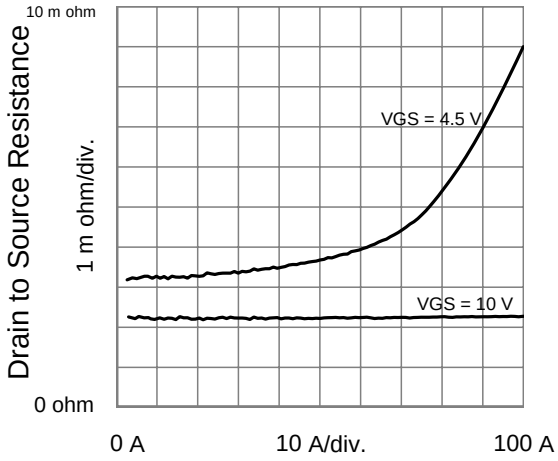

Drain to Source Voltage
Output Characteristics



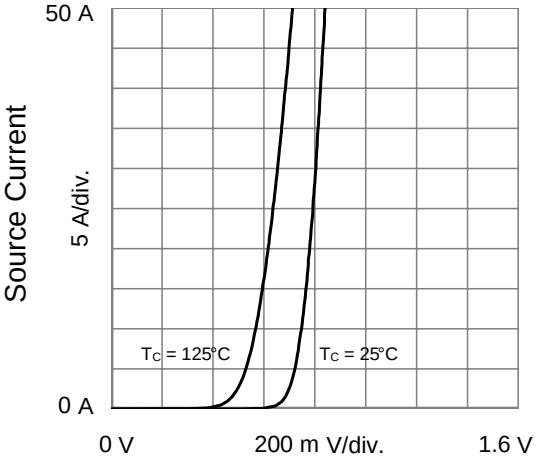

Gate to Source Voltage
Transfer Characteristics



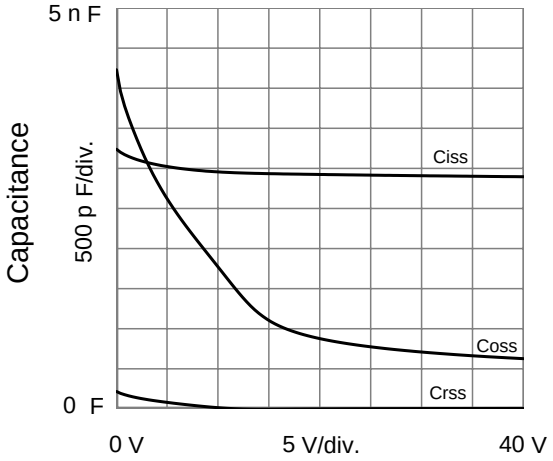

Gate to Source Voltage
Drain to Source Resistance vs. Gate to Source Voltag




Drain Current

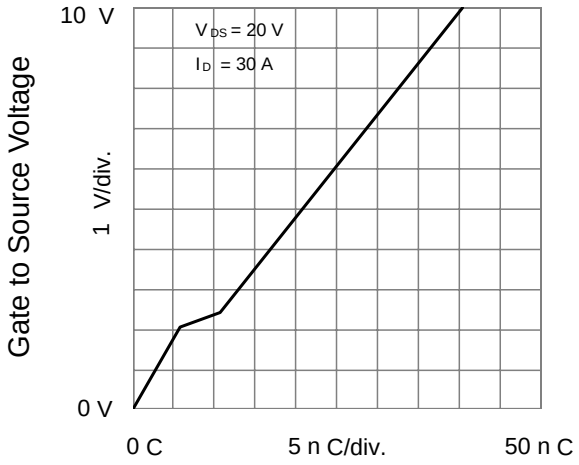



Source to Drain Voltage
Body Diode Forward Characteristics

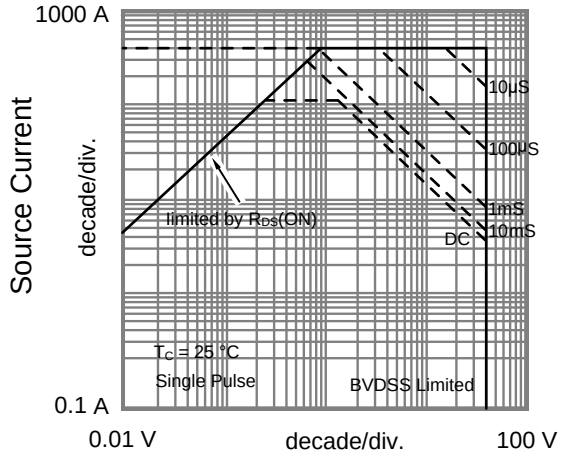



Drain to Source Voltage
Capacitances

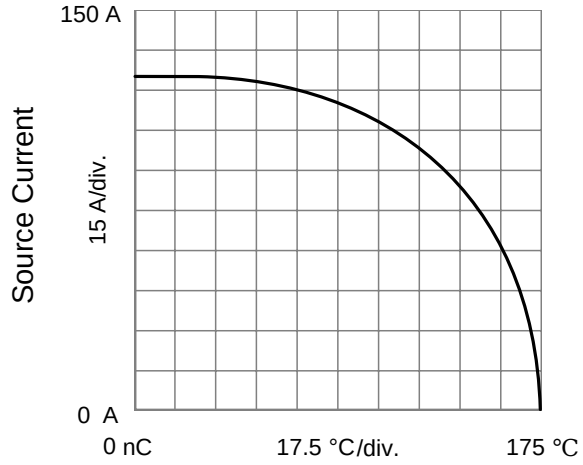
**TYPICAL CHARAC TERISTICS** (25 °C, unless otherwise noted)

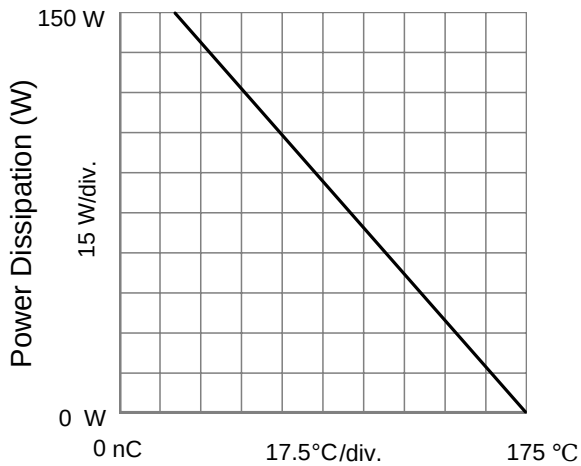


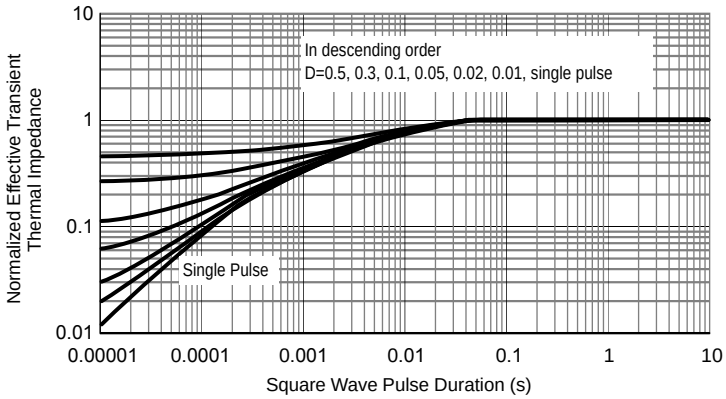

Gate to Source Voltage vs. GateCharge




Safe Operating Area, Junction-to-Case

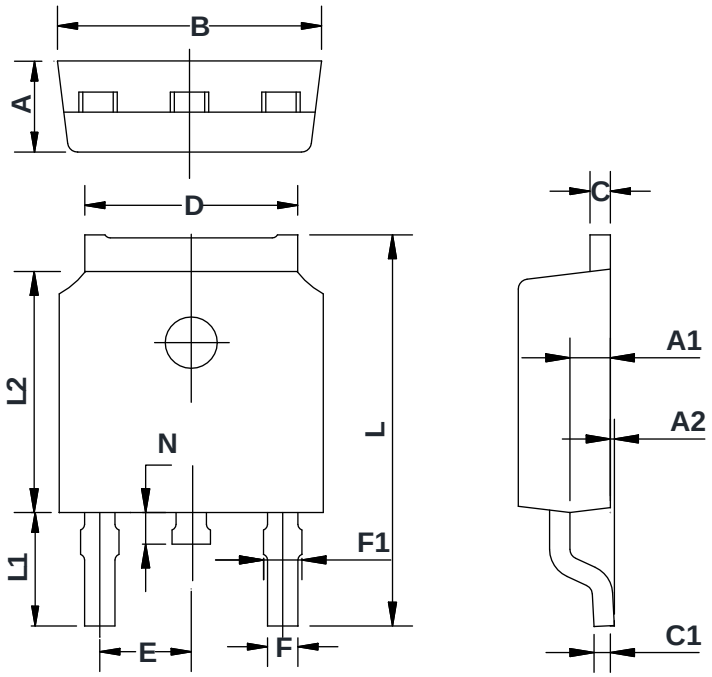



**Normalized Thermal Transient Impedance, Junction-to-Case**

# TO-252−2L PACKAGE OUTLINE




COMMON DIMENSIONS
(UNITS OF MEA SURE=MILLIMETER)

| Symbol | Min | Typ | Max |
|---|---|---|---|
| A | 2.10 | 2.30 | 2.50 |
| A1 | 0.88 | 1.01 | 1.16 |
| A2 | 0.00 | 0.15 | 0.28 |
| B | 6.40 | 6.60 | 6.80 |
| C | 0.42 | 0.50 | 0.63 |
| C1 | 0.42 | 0.50 | 0.63 |
| D | 5.08 | 5.32 | 5.65 |
| E | | 2.286 TYP | |
| F | 0.63 | 0.76 | 0.89 |
| F1 | 0.64 | 0.86 | 1.08 |
| L | 9.30 | 9.90 | 10.80 |
| L1 | 2.40 | 2.80 | 3.60 |
| L2 | 5.90 | 6.10 | 6.55 |
| N | 0.57 | 0.80 | 1.05 |

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